Product data sheet

1. General description

Enhanced ultrafast power diode in a TO252 (DPAK) surface-mountable plastic package.

2. Features and benefits

- High thermal cycling performance
- Low on-state losses
- · Low thermal resistance
- Soft recovery characteristic
- Surface-mountable package

3. Applications

- Dual mode (DCM and CCM) Power Factor Correction (PFC)
- Power Factor Correction (PFC) for Interleaved Topology
- U-inverter (DC-AC converter for individual solar panels)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_R	reverse voltage	DC	-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 115 °C; square-wave pulse; Fig. 1; Fig. 2	-	-	9	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; $T_{mb} \le$ 115 °C; square-wave pulse	-	-	18	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	-	-	91	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	-	-	100	Α
Static chara	cteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 5</u>	_	1.45	1.9	V
		I _F = 8 A; T _j = 150 °C	-	1.25	1.7	V
Dynamic ch	aracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$	-	17.5	35	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected	mb	K — A
2	K	cathode[1]		001aaa020
3	Α	anode		
mb	К	mounting base; connected to cathode	DPAK (TO252N)	

^[1] It is not possible to connect to pin 2 of the SOT428 package.

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYV29FD-600	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	TO252N			

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 115 °C; square-wave pulse; Fig. 1; Fig. 2	-	9	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le 115$ °C; square-wave pulse	-	18	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	-	91	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	-	100	A
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

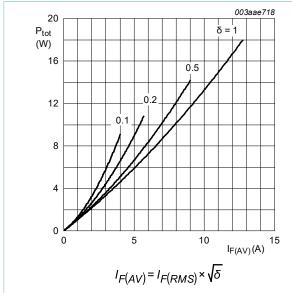


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

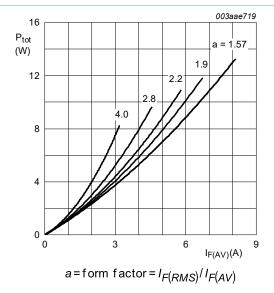


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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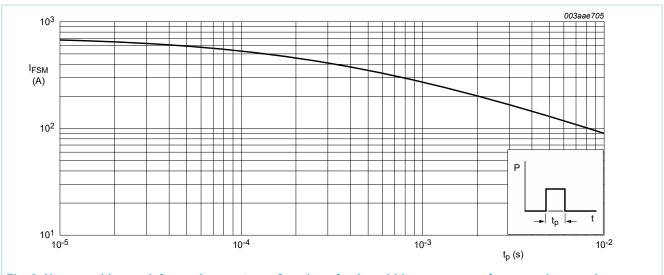


Fig. 3. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	-	2.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

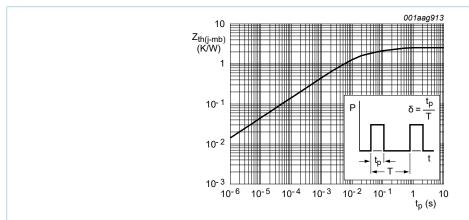


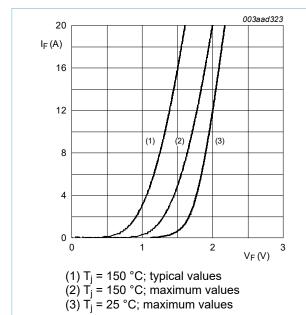
Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.45	1.9	V
		I _F = 8 A; T _j = 150 °C	-	1.25	1.7	V
I _R	reverse current	V _R = 600 V; T _j = 100 °C	-	-	1.5	mA
		V _R = 600 V; T _j = 25 °C	-	-	50	μΑ
Dynamic ch	naracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 6	-	17.5	35	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; Fig. 6	-	1.5	-	А
Q _r	recovered charge		-	13	-	nC
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 100 \text{ A/}\mu\text{s}; Fig. 6$	-	3.2	-	V





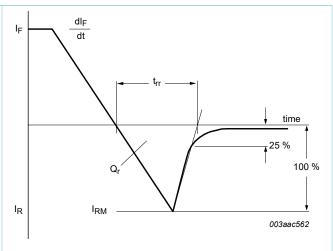
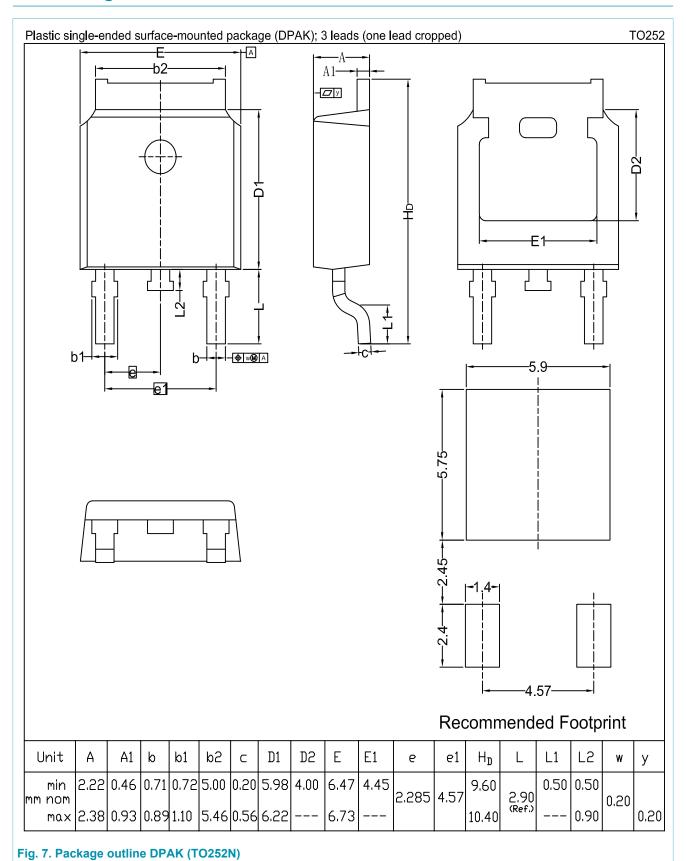


Fig. 6. Reverse recovery definitions; ramp recovery

10. Package outline



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11. Revision history

Table 6. Revision history

Document ID	Date	Changes
BYV29FD-600 Rev.01	20110307	Initial release
BYV29FD-600 Rev.02	20170815	 The format of this data sheet has been redesigned to comply with the new identity guidelines of WeEn Semiconductors. Legal texts have been adapted to the new company name where appropriate. Update "Package outline" due to subcon transfer.
BYV29FD-600 Rev.03	20171122	 Add version number and revision history on this datasheet. Update "SOT428" to "TO252" on "General description" section.

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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